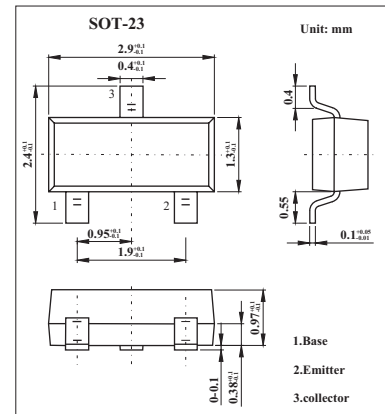


NPN General Purpose Transistors

BCX70 series

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 45 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	45	V
Collector-emitter voltage	V_{CE0}	45	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	100	mA
Peak collector current	I_{CM}	200	mA
Peak base current	I_{BM}	200	mA
Collector dissipation	P_C	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating ambient temperature	T_{amb}	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th(j-a)}$	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BCX70 series

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	ICBO	IE = 0; VCB = 45 V			20	nA
	ICBO	IE = 0; VCB = 45 V; Tj = 150 °C			20	μA
Emitter cutoff current	IEBO	IC = 0; VEB = 4 V			20	nA
	BCX70G	hFE	IC = 10 μA; VCE = 5 V			
	BCX70H			40		
	BCX70J			30		
	BCX70K			100		
DC current gain	BCX70G	hFE	IC = 2 mA; VCE = 5 V			
	BCX70H			120		220
	BCX70J			180		310
	BCX70K			250		460
DC current gain	BCX70G	hFE	IC = 50 mA; VCE = 1 V			
	BCX70H			380		630
	BCX70J			50		
	BCX70K			70		
Collector-emitter saturation voltage	VCE(sat)	IC = 10 mA; IB = 0.25 mA	50		350	mV
		IC = 50mA; IB = 1.25 mA	100		550	mV
Base to emitter saturation voltage	VBE(sat)	IC = 10 mA; IB = 0.25 mA	600		850	mV
		IC = 50mA; IB = 1.25 mA	700		1050	mV
Base to emitter voltage	VBE	IC = 2 mA; VCE = 5 V	550	650	750	mV
Collector capacitance	Cc	IE = ie = 0; VCB = 10 V; f = 1 MHz		1.7		pF
Emitter capacitance	Ce	IC = ic = 0; VEB = 0.5 V; f = 1 MHz		11		pF
Transition frequency *	ft	IC = 10 mA; VCE = 5 V; f = 100 MHz	100	250		MHz
Noise figure	NF	IC = 200 μA; VCE = 5 V; Rs = 2 kΩ; f = 1 kHz; B = 200 Hz		2	6	dB

* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ hFE Classification

Type Number	BCX70G	BCX70H	BCX70J	BCX70K
Marking	AG	AH	AJ	AK